



30V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C		
30V	6mΩ @ V _{GS} = 10V	60A		
30 V	9mΩ @ V _{GS} = 4.5V	48A		

Description

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- **Power Management Functions**
- Analog Switch

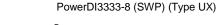
Features

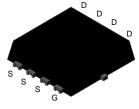
- Low RDS(ON) Ensures On-State Losses are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher **Density End Products**
- Occupies just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- 100% Unclamped Inductive Switching (UIS) Test in Production -Ensures More Reliable and Robust End Application
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free, "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

https://www.diodes.com/quality/product-definitions/

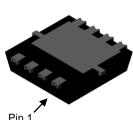
Mechanical Data

- Case: PowerDI®3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (63)
- Weight: 0.03 grams (Approximate)

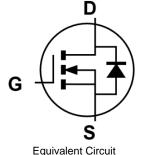




Top View







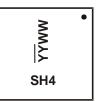
Ordering Information (Note 4)

Part Number	Case	Packaging
DMT35M4LFVW-7	PowerDI3333-8 (SWP) (Type UX)	2,000/Tape & Reel
DMT35M4LFVW-13	PowerDI3333-8 (SWP) (Type UX)	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



SH4 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 20 = 2020) WW = Week Code (01 to 53)



Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	VDSS	30	V		
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Prain Current V 40V (Note 6)	Steady State	$T_A = +25$ °C $T_A = +70$ °C	lo	16 13	А
Continuous Drain Current, V _{GS} = 10V (Note 6)	Steady State	$T_C = +25$ °C $T_C = +70$ °C	lo	60 48	А
Maximum Body Diode Forward Current (Note 6)	Is	2.3	Α		
Pulsed Drain Current (380µs Pulse, Duty Cycle = 19	I _{DM}	110	Α		
Pulsed Drain Body Diode Forward Current (380µs F	I _{SM}	110	Α		
Avalanche Current (L = 0.1mH) (Note 8)	las	22	Α		
Avalanche Energy (L = 0.1mH) (Note 8)	Eas	25	mJ		

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		PD	1.5	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	RθJA	83.3	°C/W
Total Power Dissipation (Note 6)		PD	2.2	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	RθJA	55	°C/W
Thermal Resistance, Junction to Case (Note 7)		R ₀ JC	3.9	C/VV
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

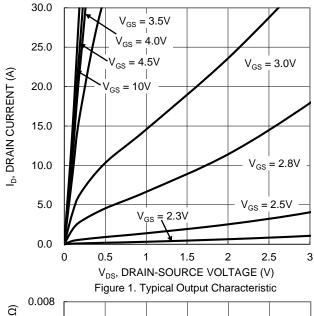
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)					l .		
Drain-Source Breakdown Voltage	BV _{DSS}	30	_	_	V	$V_{GS} = 0V, I_{D} = 250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	1	μA	$V_{DS} = 24V, V_{GS} = 0V$	
Gate-Source Leakage	lgss	_	_	±100	nA	Vgs = ±20V, Vps = 0V	
ON CHARACTERISTICS (Note 9)						•	
Gate Threshold Voltage	Vgs(TH)	1.15	_	2.5	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	4.6	6	mΩ	V _G S = 10V, I _D = 20A	
Static Diani-Source On-Resistance			6.5	9		$V_{GS} = 4.5V, I_D = 15A$	
Diode Forward Voltage	VsD	_	0.7	1	V	V _G S = 0V, I _S = 1A	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss	_	982	_		V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz	
Output Capacitance	Coss	_	903	_	pF		
Reverse Transfer Capacitance	Crss	_	27	_			
Gate Resistance	Rg	_	2.2	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1.0MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	7.9	_			
Total Gate Charge (V _{GS} = 10V)	Qg	_	16.1	_	nC	V _{DD} = 15V, I _D = 9A	
Gate-Source Charge	Q _{gs}	_	3.6	_	IIC		
Gate-Drain Charge	Qgd	_	1.2	_			
Turn-On Delay Time	t _{D(ON)}	_	8.1	_		$V_{DD} = 15V, V_{GS} = 10V,$ $R_g = 3\Omega, I_D = 9A$	
Turn-On Rise Time	t _R	_	2.2	_			
Turn-Off Delay Time	tD(OFF)	_	16.8	_	ns		
Turn-Off Fall Time	tF	_	5.7	_			

5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided. Notes:

- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
- 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 9. Short duration pulse test used to minimize self-heating effect.
 10. Guaranteed by design. Not subject to product testing.





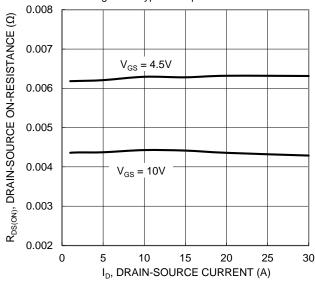


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

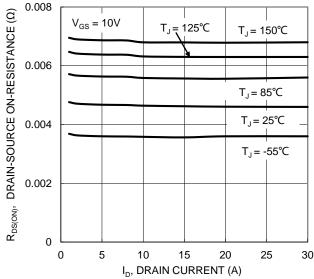
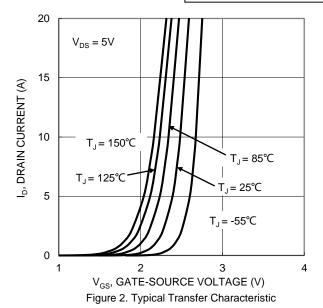


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

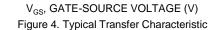


0.1 $R_{\mathrm{DS}(ON)},$ DRAIN-SOURCE ON-RESISTANCE (Ω) 0.09 $I_D = 20A$ 0.08 0.07 $I_{D} = 15A$ 0.06 0.05 0.04 0.03

0.02

0.01

0 2



10 12 14 16 18

8

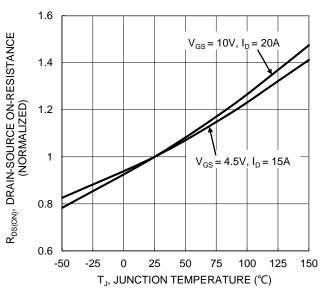


Figure 6. On-Resistance Variation with Junction Temperature





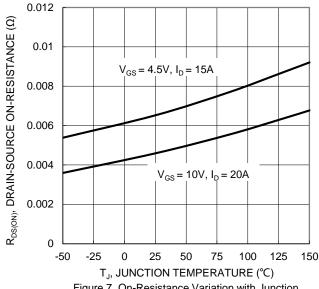
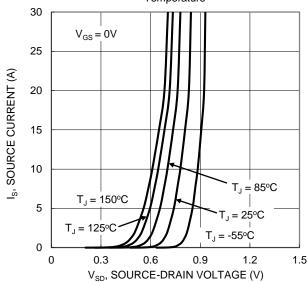
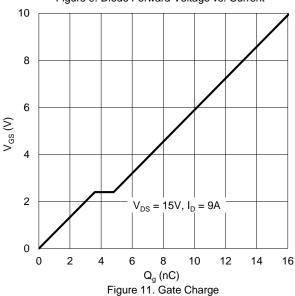


Figure 7. On-Resistance Variation with Junction Temperature



V_{SD}, SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current



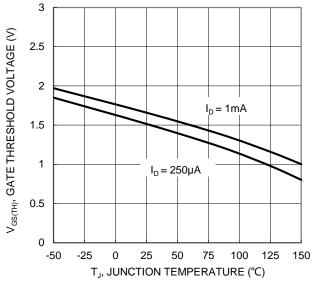
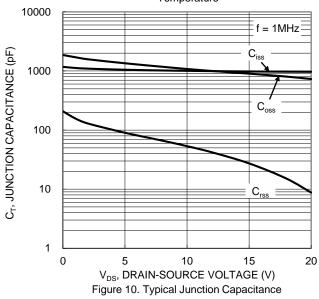


Figure 8. Gate Threshold Variation vs. Junction Temperature



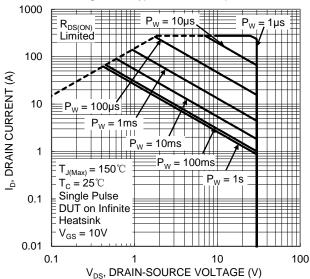


Figure 12. SOA, Safe Operation Area

June 2020



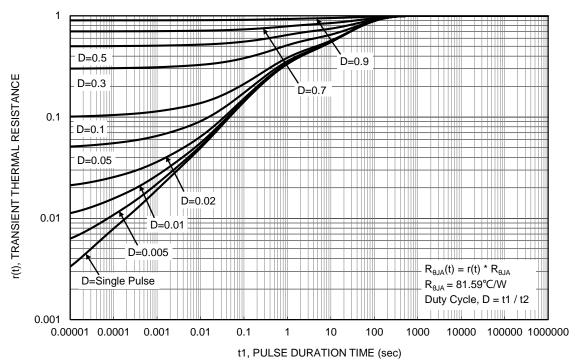


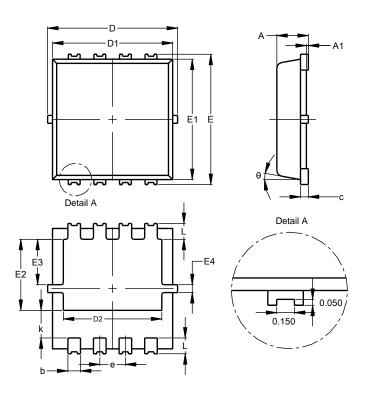
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)

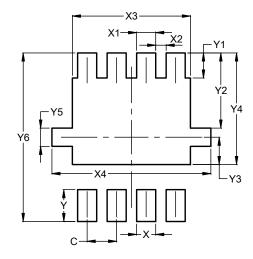


PowerDI3333-8 (SWP)							
	(Type UX)						
Dim	Min Max Ty						
Α	0.75	0.85	0.80				
A1	0.00	0.05					
b	0.25	0.40	0.32				
С	0.10	0.25	0.15				
D	3.20	3.40	3.30				
D1	2.95	3.15	3.05				
D2	2.30	2.70	2.50				
Е	3.20	3.40	3.30				
E1	2.95	3.15	3.05				
E2	1.60	2.00	1.80				
E3	0.95	1.35	1.15				
E4	0.10	0.30	0.20				
е	_	_	0.65				
k	0.50	0.90	0.70				
L	0.30	0.50	0.40				
θ	0°	12°	10°				
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)			
С	0.650			
Х	0.420			
X1	0.420			
X2	0.230			
Х3	2.600			
X4	3.500			
Υ	0.700			
Y1	0.550			
Y2	1.650			
Y3	0.600			
Y4	2.450			
Y5	0.400			
Y6	3.700			



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